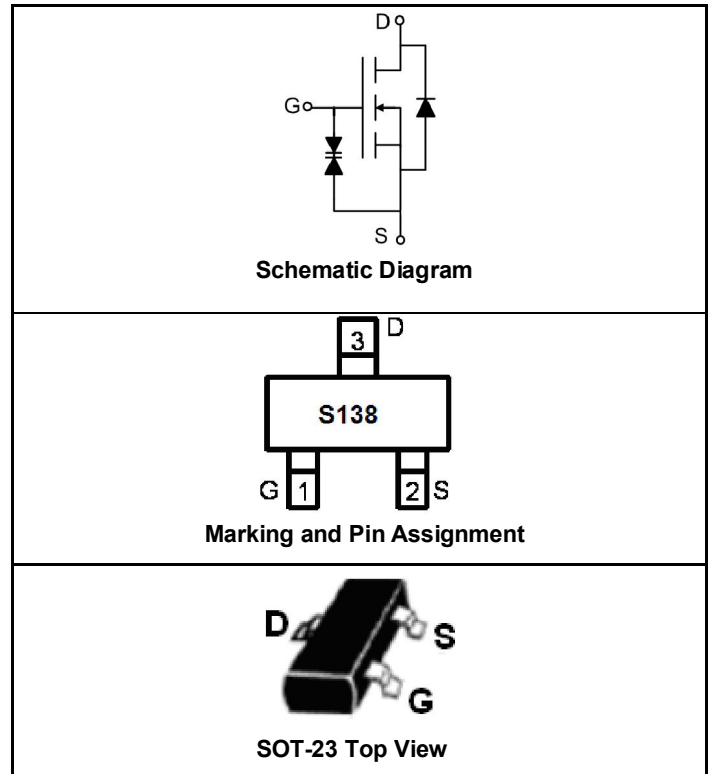


GENERAL FEATURES

- $V_{DS} = 50V, I_D = 0.22A$
- $R_{DS(ON)} < 6\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} < 3.5\Omega @ V_{GS}=10V$
- ESD Rating: 1000V HBM
- High Power and current handing capability
- Lead free product
- Surface Mount Package

APPLICATIONS

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



PACKAGE MARKING AND ORDERING INFORMATION

| Device Marking | Device | Device Package | Reel Size | Tape Width | Quantity |
|----------------|--------|----------------|-----------|------------|------------|
| S138 | BSS138 | SOT-23 | Ø180mm | 8 mm | 3000 units |

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|-------------------------|------------|------------------|
| Drain-Source Voltage | V_{DS} | 50 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous@ Current-Pulsed (Note 1) | I_D | 0.22 | A |
| | $I_D(70^\circ\text{C})$ | 0.18 | |
| | I_{DM} | 0.88 | A |
| Maximum Power Dissipation | P_D | 0.43 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| | | | |
|--|-----------------|-----|--------------------|
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 350 | $^\circ\text{C/W}$ |
|--|-----------------|-----|--------------------|

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|----------------------------|--------|-----------|-----|-----|-----|------|
| OFF CHARACTERISTICS | | | | | | |



BSS138

50V N-Channel MOSFET

| | | | | | | |
|---|--------------|--|----------|-----|-----|----------|
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 50 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=50V, V_{GS}=0V$ | | | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | | | 10 | μA |
| Gate-Source Breakdown Voltage | BV_{GSO} | $V_{DS}=0V, I_G=\pm 250\mu A$ | ± 20 | | | V |
| ON CHARACTERISTICS (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=1mA$ | 0.8 | | 1.5 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=0.22A$ | | | 3.5 | Ω |
| | | $V_{GS}=4.5V, I_D=0.22A$ | | | 6 | |
| Forward Transconductance | g_{FS} | $V_{DS}=10V, I_D=0.22A$ | | 0.1 | | S |
| DYNAMIC CHARACTERISTICS (Note4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=25V, V_{GS}=0V, F=1.0MHz$ | | 30 | | PF |
| Output Capacitance | C_{oss} | | | 15 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 6 | | |
| SWITCHING CHARACTERISTICS (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=30V, V_{GS}=10V, R_{GEN}=6\Omega, I_D=0.22A$ | | 2.6 | | nS |
| Turn-On Rise Time | t_r | | | 9 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 20 | | |
| Turn-Off Fall Time | t_f | | | 6 | | |
| Total Gate Charge | Q_g | $V_{DS}=25V, I_D=0.22A, V_{GS}=10V$ | | 1.7 | 2.4 | nC |
| Gate-Source Charge | Q_{gs} | | | 0.1 | | |
| Gate-Drain Charge | Q_{gd} | | | 0.4 | | |
| DRAIN-SOURCE DIODE CHARACTERISTICS | | | | | | |
| Diode Forward Voltage (Note 3) | V_{SD} | $V_{GS}=0V, I_S=0.44A$ | | | 1.4 | V |

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

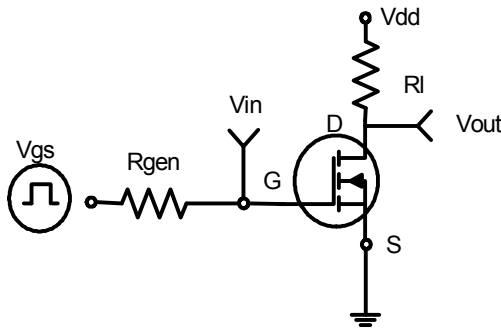


Figure 1: Switching Test Circuit

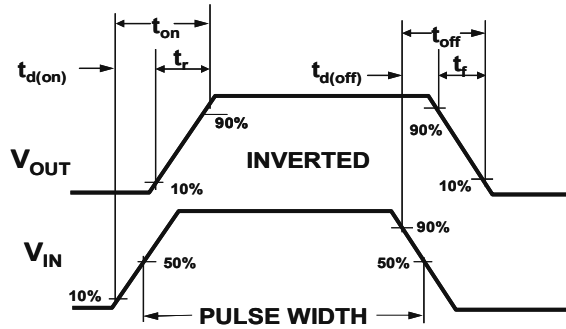


Figure 2: Switching Waveforms

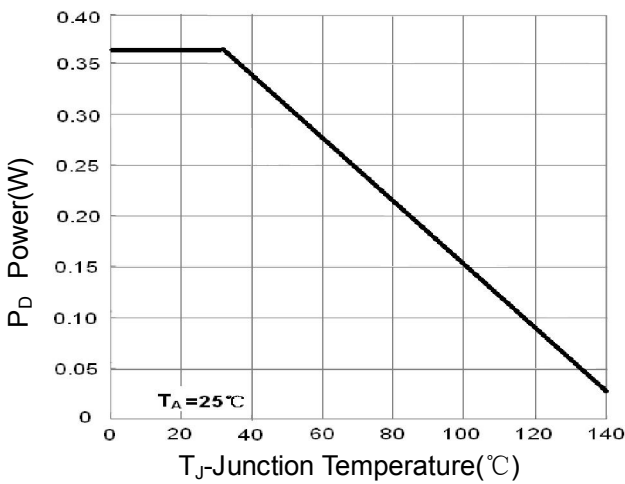


Figure 3 Power Dissipation

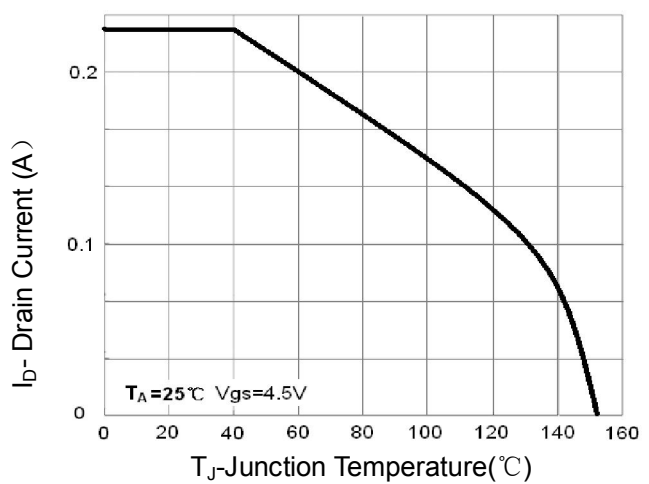


Figure 4 Drain Current

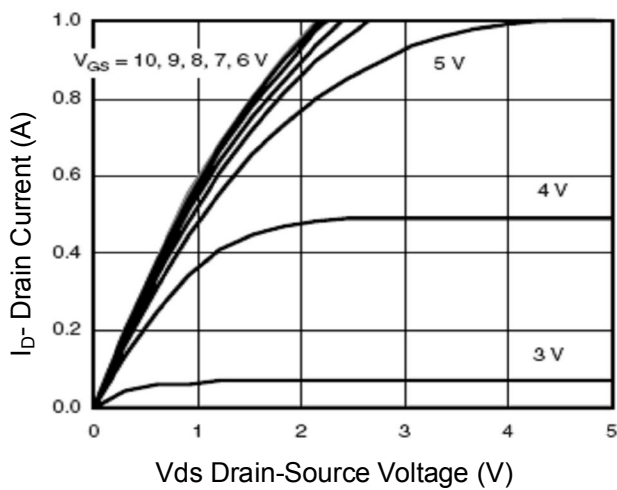


Figure 5 Output CHARACTERISTICS

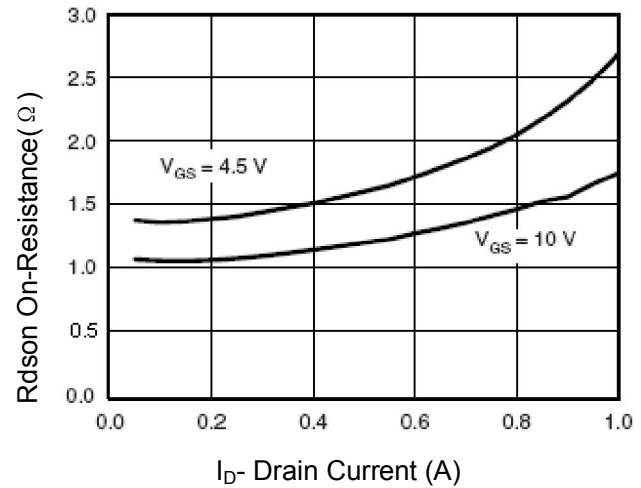


Figure 6 Drain-Source On-Resistance

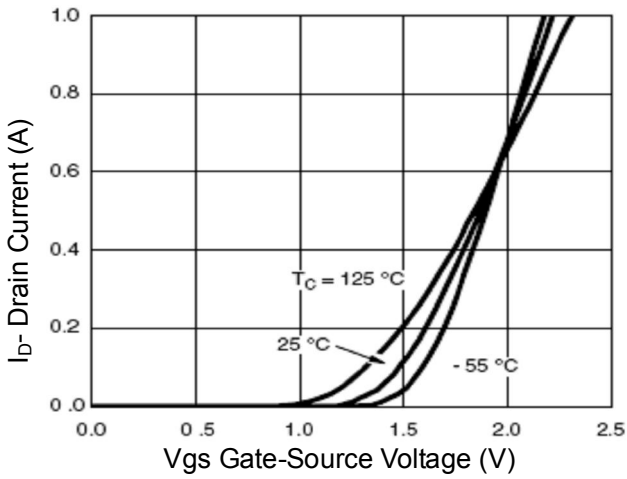


Figure 7 Transfer Characteristics

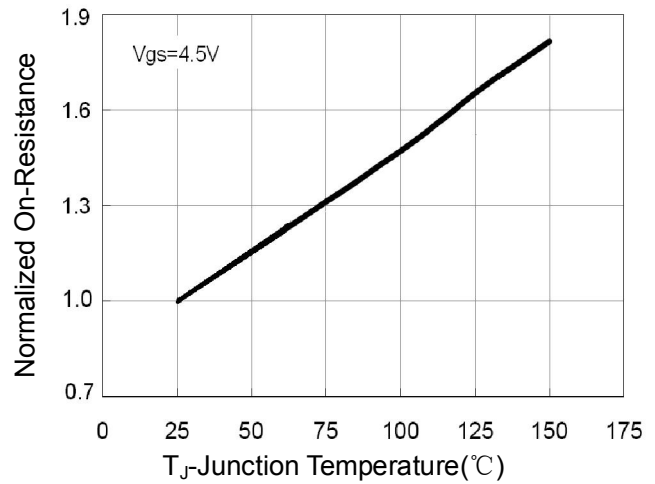


Figure 8 Drain-Source On-Resistance

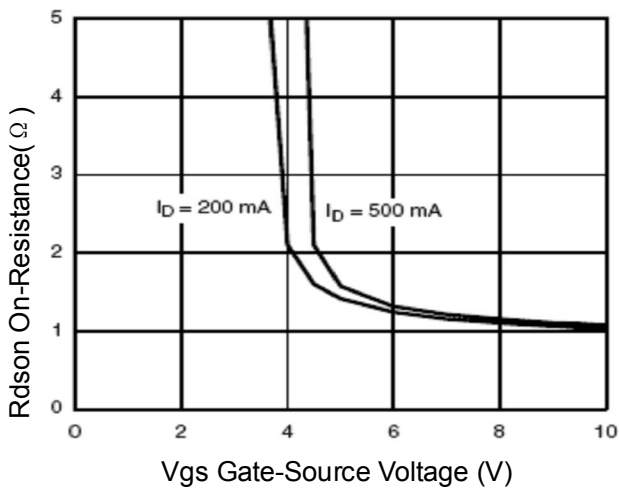


Figure 9 Rdson vs Vgs

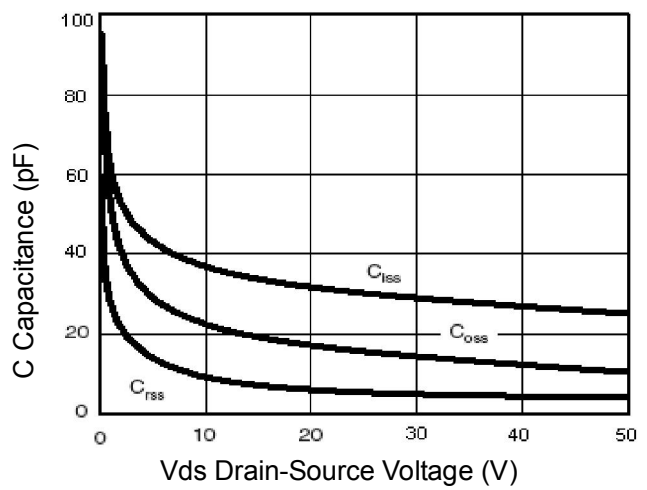


Figure 10 Capacitance vs Vds

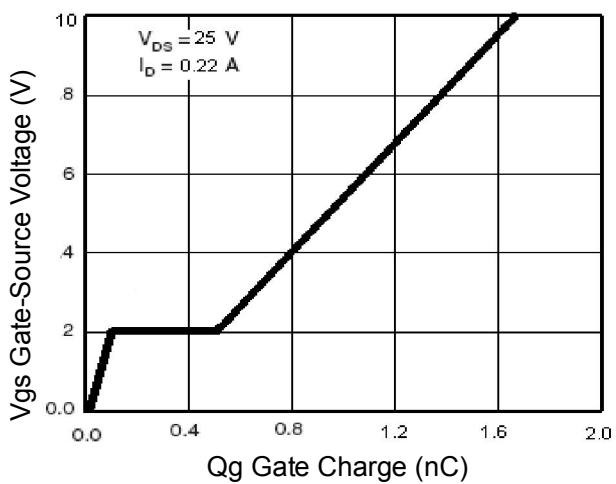


Figure 11 Gate Charge

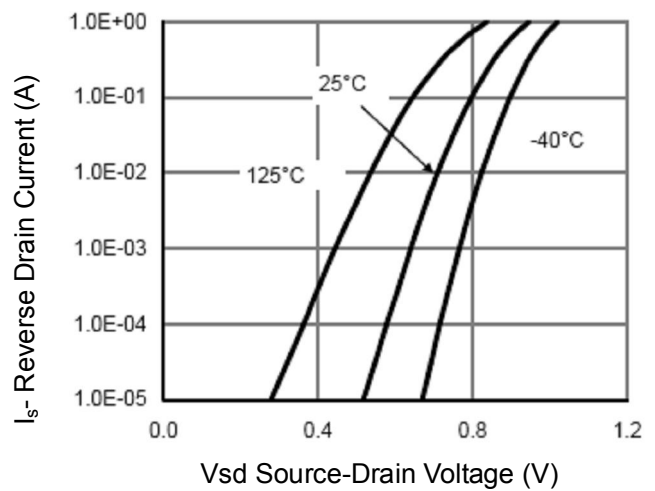


Figure 12 Source- Drain Diode Forward

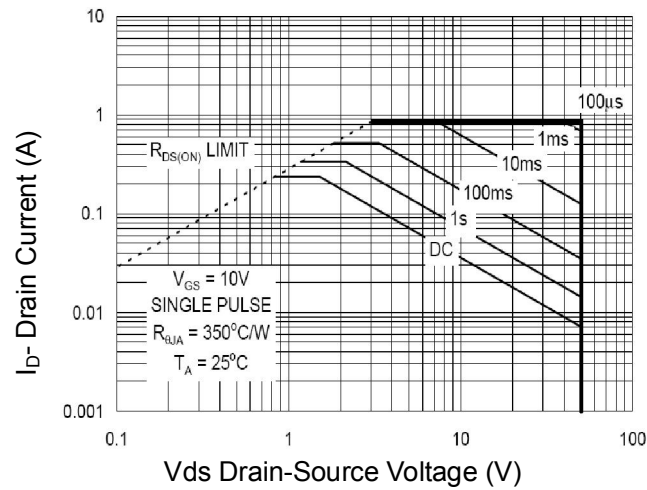


Figure 13 Safe Operation Area

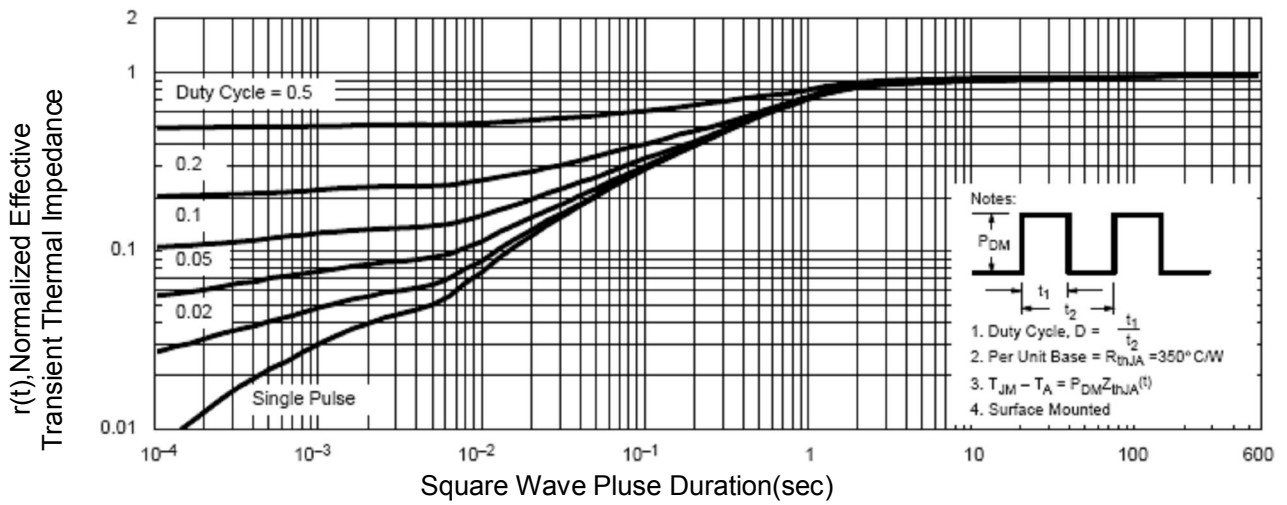
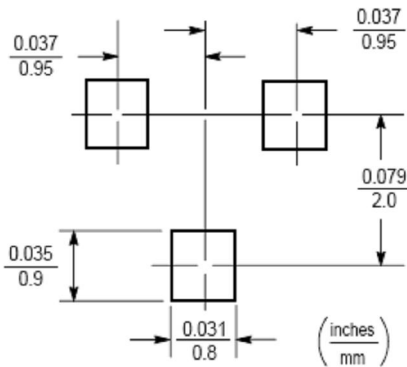
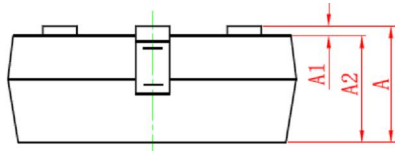
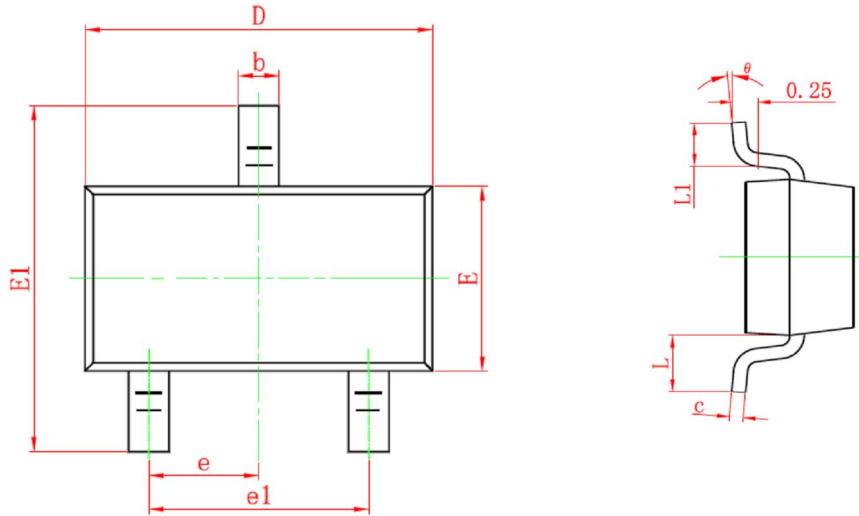


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT: mm)



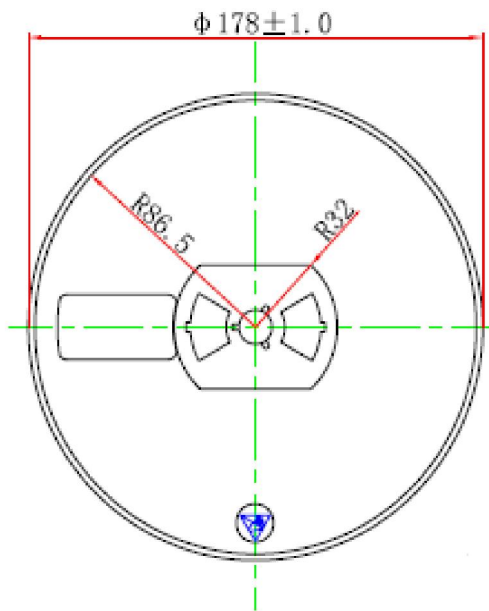
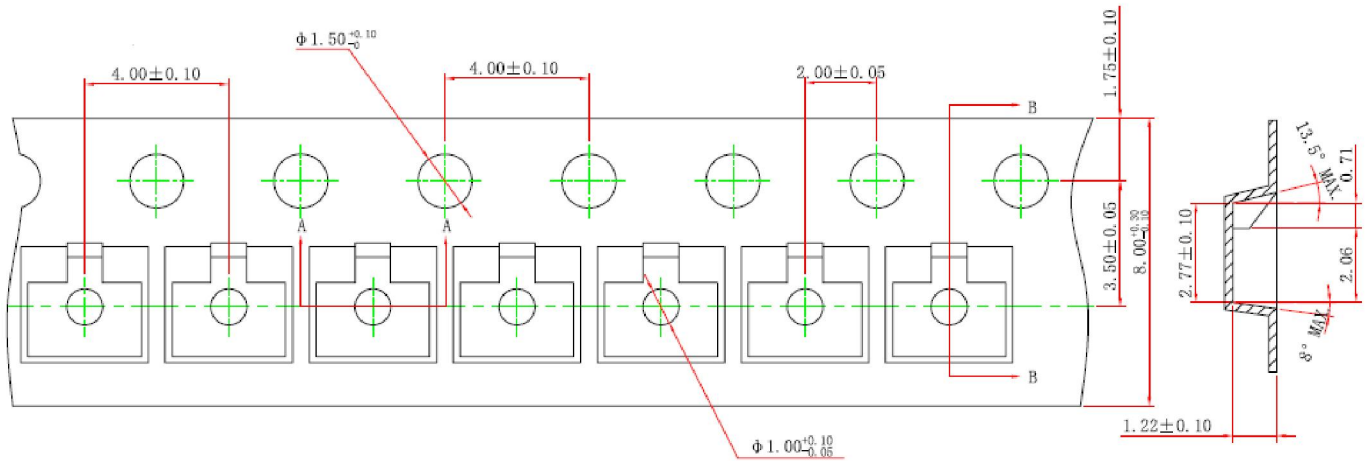
| Symbol | Dimensions in Millimeters | |
|----------|---------------------------|-------|
| | MIN. | MAX. |
| A | 0.900 | 1.150 |
| A1 | 0.000 | 0.100 |
| A2 | 0.900 | 1.050 |
| b | 0.300 | 0.500 |
| c | 0.080 | 0.150 |
| D | 2.800 | 3.000 |
| E | 1.200 | 1.400 |
| E1 | 2.250 | 2.550 |
| e | 0.950TYP | |
| e1 | 1.800 | 2.000 |
| L | 0.550REF | |
| L1 | 0.300 | 0.500 |
| θ | 0° | 8° |

NOTES

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

SOT 23 Tape and Reel Information

Dimensions in Millimeters (UNIT: mm)



NOTES:

1. All dimensions are in millimeters.
2. 10 Sprocket hole pitch cumulative tolerance $\pm 0.20 \text{ MAX}$
3. General tolerance ± 0.25